

Ultra high stability temperature compensated crystal oscillator Product name : TG5032CFN / TG5032SFN

Features

● Ultra high stability (< 0.1 x 10⁻⁶)

Low phase noise

Frequency range: 10 MHz to 40 MHz
Output: CMOS, Clipped sine wave
Supply voltage: 2.375 to 3.63 V

External dimensions: 5.0 x 3.2 x 1.45 mm

Small size package (4 pads)

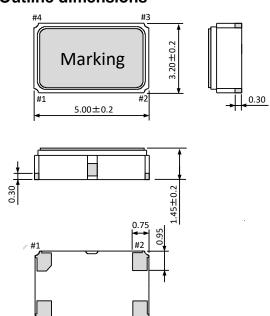
Pb free.

Complies with EU RoHS directive.

Applications

- Small Cells
- Stratum3
- Femtocell
- Network system etc..

Outline dimensions



Pin information

Pin	Connections						
FIII	VC-TCXO	TCXO					
1	Vc	N.C.					
2	GND						
3	OUT						
4	Vcc						



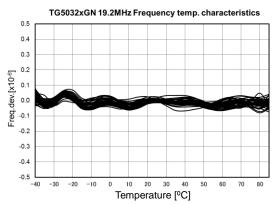
Description

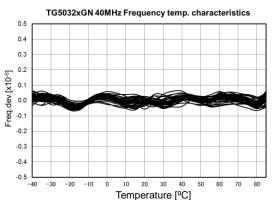
This product is ultra high stability temperature compensated crystal oscillator of CMOS and Clipped sine wave outputs using fundamental oscillation of Crystal unit. This has realized a low phase noise in frequency 10 to 40 MHz, and it is suitable for the reference clock include Small Cells.

This allows the product to be compliant with various standards including GR-1244-CORE Stratum3, G.8262.1, G.8273.2(Class A,B).

Characteristics

Frequency / temperature characteristics







1. Product Number / Product Name

(1-1) Product Number / Ordering Code

TG5032CFN: X1G005391xxxx00 (Please contact Epson for details of number xxxx)

TG5032SFN: X1G005401xxxx00 (The last 2 digits code (00) define Quantity. 1 000 pcs/Reel)

(1-2) Product Name / Model Name (Standard form)

TG5032CFN 10.000000MHz CAGNDA

1 2 3 456789

1 Model

2 Output

3 Frequency

4 Supply voltage

⑤ Frequency / temperature

6 Operation temperature

7 OE function (H: Non)

8 Vc function (Non Filter)

Internal identification code ("A" is default)

2	Output
O	CMOS
S	Clipped sine Wave

4 Supply voltage

3.3 V

5	Frequency / temperature
Α	±0.1 x 10 ⁻⁶
В	±0.28 x 10 ⁻⁶

6	Operation temperature
G	-40 °C to +85 °C

7	OE function
Ν	Non OE function

2. Electrical characteristics

1) Absolute maximum ratings

Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
Supply voltage	Vcc-GND	V	-0.5	-	+4.0	
Storage temperature	T_stg	°C	-40	-	+90	Store as bare product after packing
Frequency control voltage	V _C -GND	V	-0.5	-	V _{CC} +0.5	V _C Terminal

2) Operating conditions

Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
	\/		2.375	-	3.63	Supply voltage range
Supply voltage	Vcc	V	2.85	3.0	3.15	Vcc=3.0 V Type
	GND		0.0	-	0.0	
Operating temperature range	T_use	°C	-40	+25	+85	Standard
			GND	N.C.	-	V _C Terminal / TCXO
Frequency control voltage	Vc	V	0.5	1.5	2.5	V _C Terminal / VC-TCXO
			0.65	1.65	2.65	
	Load_C	pF	13.5	15	16.5	CMOS output
	Load_C	рF	9	10	11	Clipped sine wave
Output load condition	Load_R	kΩ	9	10	11	Clipped sine wave
	Сс	μF	0.01	-	-	DC-cut capacitor *1 Clipped sine wave

^{*1} DC-cut capacitor is not included in this TCXO. Please attach an external DC-cut capacitor (0.01 µF Min.) to the out pin.

3-1) Frequency characteristics

(Vcc = Tvp)	GND = 0.0	V Vc = Tvp	V Load = Tvp	., T use = $+25$ °C)
(VOO-I)P.	O110 - 0.0	v, vo — 1 yp	. v, Loau - 1 yp	., 1 436 - 120 01

December Cymbol Unit						Notes
Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
Output frequency	fo	MHz			40 24,576, 25, 1, 38.88, 40	Standard frequency list
Frequency tolerance *2 (T_use=+25 °C +/-2 °C) (Reflow cycles : 2 times)	f_tol	× 10 ⁻⁶	-1.0	-	+1.0	
Fragues av / temperature			-0.10	-	+0.10	T_use=-40 °C to +85 °C (Standard)
Frequency / temperature characteristics	fo-Tc	× 10⁻ ⁶	-0.14	1	+0.14	T_use=-40 °C to +85 °C
(Reference to (fmax+fmin)/2.)	10-10	X 10 °	-0.25	-	+0.25	T_use=-40 °C to +85 °C
(Reference to (imax+imin)/2.)			-0.28	-	+0.28	T_use=-40 °C to +85 °C
Fraguency / load coefficient	fo-Load	× 10 ⁻⁶	-0.10	-	+0.10	Load +/-10 %
Frequency / load coefficient	10-Loau	× 10 °	-0.05	-	+0.05	Load +/-2 %
Frequency / voltage	fo- Vcc	× 10 ⁻⁶	-0.10	-	+0.10	V _{CC} +/-5 %
coefficient	10- VCC	X 10 °	-0.05	1	+0.05	Vcc +/-2 %
Frequency slope	-	× 10 ⁻⁶ /°C	-0.10	-	+0.10	Minimum of 1 frequency reading every 2 °C, over the operating temperature range (1 °C/minute max.)
Hysteresis	-	× 10 ⁻⁶	-0.20	-	+0.20	Frequency measured before and after at +25 °C.
Fraguency aging *6	f ago	× 10 ⁻⁶	-0.5	1	+0.5	T_use=+25 °C, First year
Frequency aging *6	f_age	X 10 °	-3.0	-	+3.0	T_use=+25 °C, 20 years
Holdover stability		× 10 ⁻⁶	-0.01	-	+0.01	T_use=+25 °C, 1 day *3
(Constant temperature)	-	× 10°	-0.04	-	+0.04	T_use=+25 °C, 1 day *4
Holdover stability (Free-run accuracy)	-	× 10 ⁻⁶	-4.6	-	+4.6	*5
Acceleration sensitivity	-	× 10 ⁻⁹ / G	-	2.0	-	3 axes, 30-1500 Hz

^{*2} Measured 24 hours after reflow soldering.

^{*3} After 10 days of continuous operation.

^{*4} After 48 hours of continuous operation.

^{*5} This includes initial frequency tolerance, frequency / temperature characteristics, frequency / load coefficient, frequency/voltage coefficient and frequency aging (+25 °C , 20 years)

^{*6} Aging stability is estimated from environmental reliability tests and the expected amount of the frequency variation over time. It is not intend as a guarantee of performance over the product-life cycle

3-2) Frequency control characteristics (Vcc = Typ., GND = 0.0 V, Vc = Typ. V, Load = Typ., T_use = +25 °C)

				71.		<u> </u>
Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
Frequency control range	f cont	× 10 ⁻⁶	-10.0	-	-5.0	Vc=1.5 V+/-1.0 V, Vc=1.65 V+/-1.0 V
Frequency control range	I_COIT	X 10 °	+5.0	-	+10.0	VC=1.5 V+/-1.0 V, VC=1.05 V+/-1.0 V
Linearity	-	%	-10	-	+10	
Input impedance	Z _{IN}	kΩ	100	-	-	V_C -GND(DC), V_C =Typ.
Frequency change polarity	-	-	Positive polarity		rity	

4) Electrical Characteristics (Vcc = Typ., GND = 0.0 V, Vc = Typ. V, Load = Typ., T_use = +25 °C)

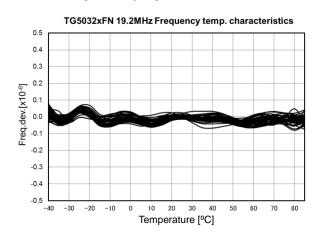
4) Electrical Chara	Cicilotics	1	(7 0 0	= Typ., GND =	0.0 v, vc =	Typ. V, Load = Typ., T_use = +25 °
Parameter	Symbol	Unit	Min.	Тур.	Max	Notes
		_	-	-	5.0	Clipped sine wave (Standard)
Current consumption		A	-	-	3.0	Clipped sine wave (Option)
Current consumption	Icc	mA	-	-	5.0	CMOS (~26 MHz)
			-	-	6.0	CMOS (~40 MHz)
Start up time	t_str	ms	-	1.0	5.0	t=0 at 90 %Vcc
Rise time	tr	ns	-	-	8.0	10 %Vcc to 90 %Vcc level CMOS output
Fall time	tf	ns	-	-	8.0	90 %Vcc to 10 %Vcc level CMOS output
O	6)///	0/	45	50	55	50 % Vcc level CMOS output
Symmetry	SYM	%	40	50	60	GND level (DC-cut) Clipped sine wave (Option)
High output voltage	Vон	V	90 % Vcc	-	-	CMOS output
Low output voltage	Vol	V	-	-	10 % Vcc	CMOS output
Output level	Vpp	V	0.8	-	-	Clipped sine wave
•	1		-	-69	-	1 Hz offset
			-	-98	-	10 Hz offset
Phase Noise 10 MHz			-	-125	-	100 Hz offset
TCXO mode	L(f)	dBc/Hz	-	-144	-	1 kHz offset
	()	GD6/112	-	-152	-	10 kHz offset
			-	-153	-	100 kHz offset
			-	-154	-	1 MHz offset
			-	-63 (-60)	-	1 Hz offset
		dBc/Hz	_	-92 (-90)	_	10 Hz offset
Phase Noise 19.2 MHz			-	-119 (-116)	-	100 Hz offset
TCXO mode	L(f)		_	-140 (-139)	-	1 kHz offset
() is VC-TCXO mode	_(.)		_	-153 (-152)	-	10 kHz offset
() 10 10 10 10 110 1110 1110 1110 1110 1			_	-154 (-154)	-	100 kHz offset
			_	-155 (-154)	-	1 MHz offset
			_	-62 (-62)	-	1 Hz offset
			_	-92 (-90)	_	10 Hz offset
Phase Noise 20 MHz			_	-119 (-117)	_	100 Hz offset
TCXO mode	L(f)	dBc/Hz	_	-140 (-138)	_	1 kHz offset
() is VC-TCXO mode	L(1)	UDC/112	_	-152 (-152)	_	10 kHz offset
() is vo-Toxo mode			_	-154 (-154)	_	100 kHz offset
				-154 (-155)	 _	1 MHz offset
			_	. ,	_	
			-	-62 (-60)	-	1 Hz offset
DI N. 05.1411			-	-93 (-90)	-	10 Hz offset
Phase Noise 25 MHz	1.00	ID ".	-	-118 (-116)	-	100 Hz offset
TCXO mode	L(f)	dBc/Hz	-	-139 (-137)	-	1 kHz offset
() is VC-TCXO mode			-	-153 (-152)	-	10 kHz offset
			-	-154 (-154)	-	100 kHz offset
			-	-156 (-156)	-	1 MHz offset
			-	-59 (-54)	-	1 Hz offset
			-	-89 (-83)	-	10 Hz offset
Phase Noise 40 MHz			-	-114 (-110)	-	100 Hz offset
TCXO mode	L(f)	dBc/Hz	-	-135 (-132)	-	1 kHz offset
() is VC-TCXO mode	_(.,	J	_	-150 (-149)	_	10 kHz offset
V			_	-152 (-152)	_	100 kHz offset
			_	-155 (-155)	_	1 MHz offset
	1	l	1	100 (100)	1	12 011000

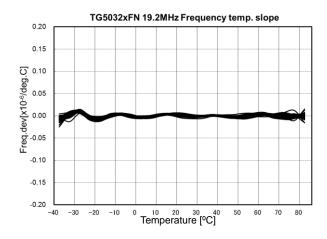


3. Characteristics

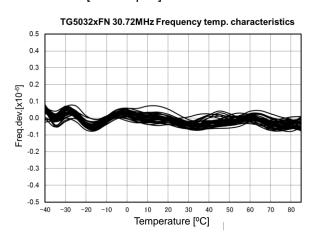
3-1) "Frequency / Temperature Characteristics" 3-1-1) Standard spec : +/-0.1 \times 10⁻⁶ Max. (T_use=-40 °C to +85 °C)

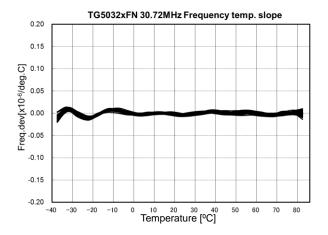
19.2 MHz [N = 40 pcs]



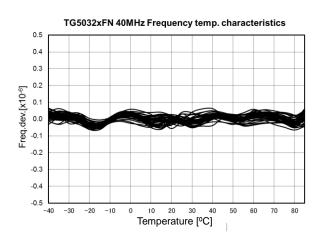


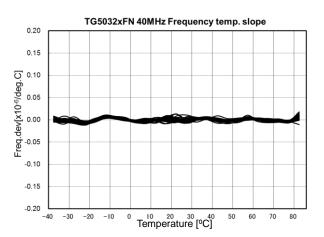
30.72 MHz [N = 40 pcs]





40 MHz [N = 40 pcs]







3-2) Frequency Aging (40 MHz) [N = 5 pcs]

* Aging is estimated from environmental reliability tests and the expected amount of frequency variation over time. It is not intended as a guarantee of performance over the product-life cycle.



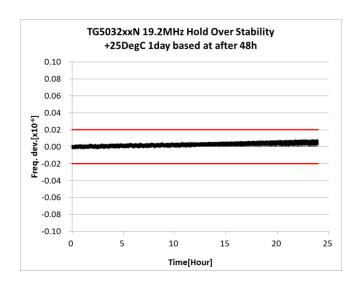
about 1year

Ave. : -0.10×10^{-6} Max. : -0.05×10^{-6} Min. : -0.12×10^{-6}

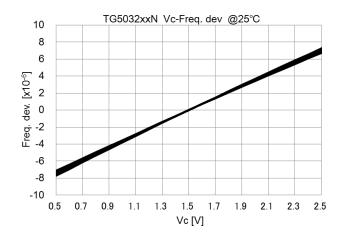
about 20years

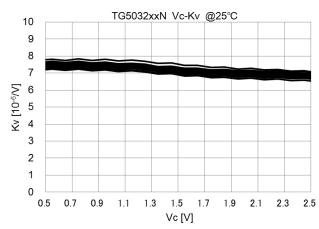
Ave. : -0.54 x 10⁻⁶ Max. : -0.35 x 10⁻⁶ Min. : -0.66 x 10⁻⁶

3-3) Holdover Stability (19.2 MHz) [N = 40 pcs]



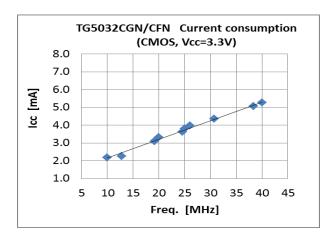
3-4) Frequency Control Characteristics [N = 40 pcs]

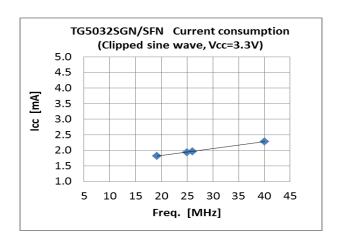




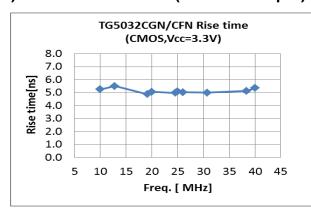


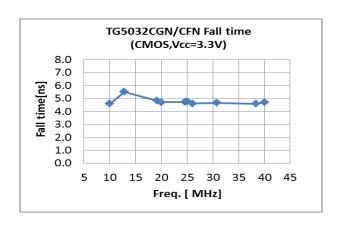
3-5) Current Consumption



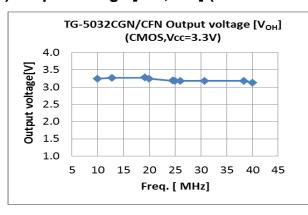


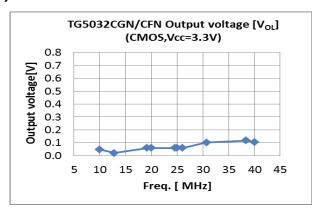
3-6) Rise time / Fall time (at CMOS output)



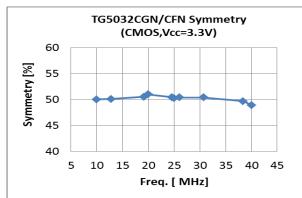


3-7) Output voltage [Voh, Vol] (at CMOS output)

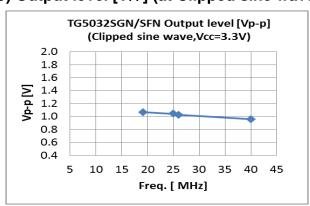




3-8) Symmetry (at CMOS output)



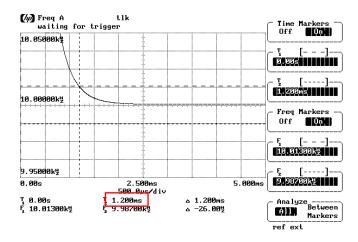
2-9) Output level [VPP] (at Clipped sine wave)



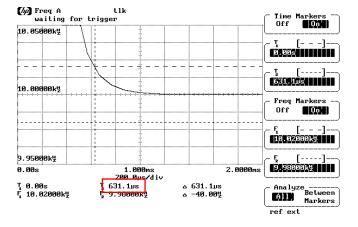


3-10) Start up time (19.2 MHz, 40 MHz)

19.2 MHz



40 MHz

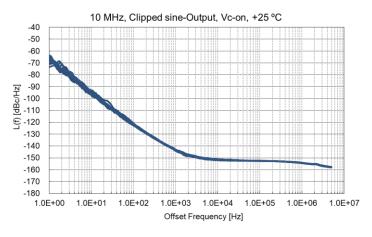


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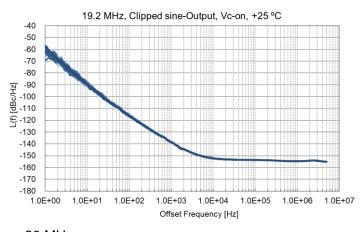


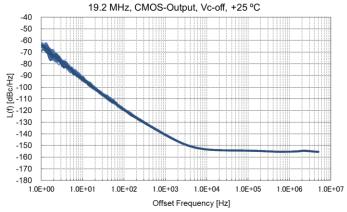
3-11) Phase noise (10 MHz, 19.2 MHz, 20 MHz) [N = 25 pcs]

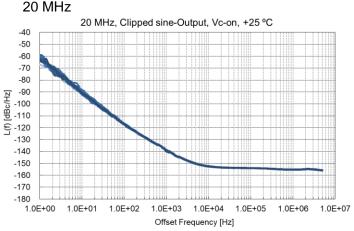
10 MHz

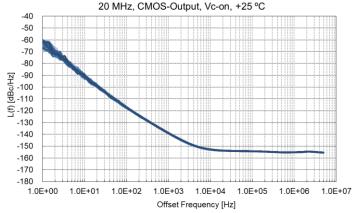


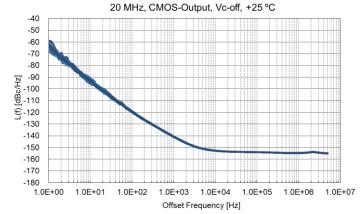
19.2 MHz







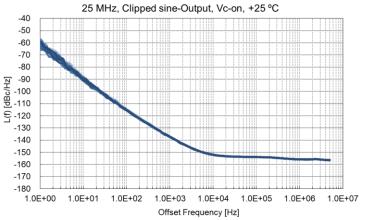


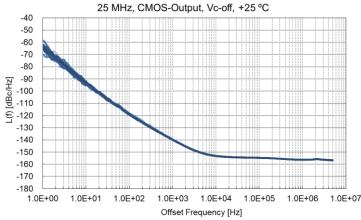




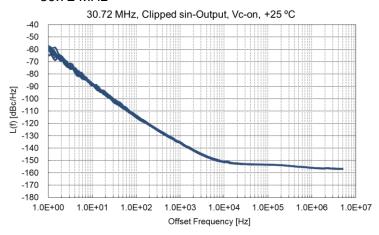
3-11) Phase noise (25 MHz, 30.72 MHz, 40 MHz) [n = 25 pcs]

25 MHz

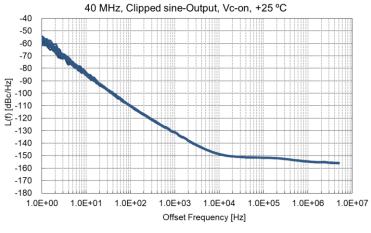


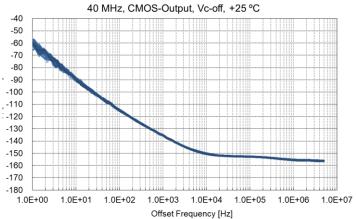


30.72 MHz



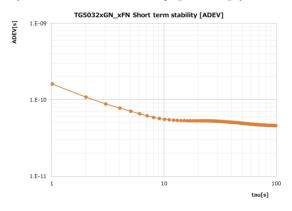
40 MHz





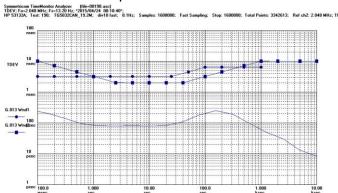


3-12) Short term stability [ADEV] (19.2 MHz) TCXO mode



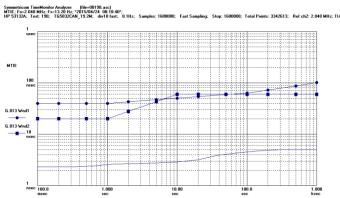
3-13) TDEV (19.2 MHz, Loop BW = 0.1 Hz)

Constant temperature: +25 °C



3-14) MTIE (19.2 MHz, Loop BW = 0.1 Hz)

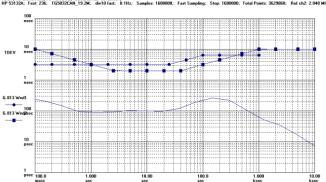
Constant temperature : +25 °C



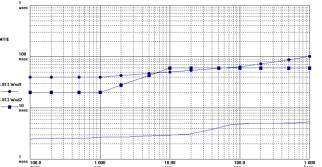
Compliant with G.813 option1 and 2

Constant temperature: +70 °C

Symmetricson TimeMoreket Analyses (18-00225.acc) 1704/Fra-20 AM INT: Fra-13 78 Hz - 1975/55/98 07:58097; 1714/Fra-15 AM INT: Fra-13 78 Hz - 1975/55/98 07:58097; 1715/Fra-15 AM INT: Fra-15 AM INT: Fra-15 AM INT: Samples: 1600000; Fast Sampling: Stop: 1600000; Total Point: 3629668; Rel ch2: 2.040 MHz; TI/Ti



Constant temperature: +70 °C

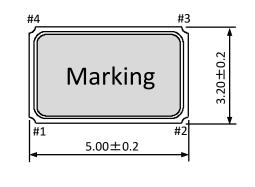


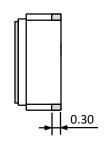


4. Outline

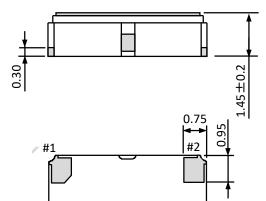
4-1) Outline dimensions and Pin information

TG5032CFN / SFN





Unit: mm



Pin	Connections						
FIII	VC-TCXO	TCXO					
1	V _C	N.C.					
2	GND						
3	OUT						
4	V _{CC}						

Do not connect "N.C." pin with any other pins (also mutually)

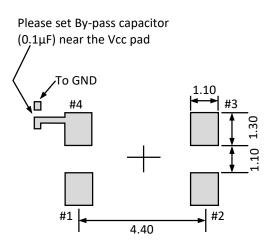
4-2) Soldering pattern

Example of patterning design indicated as follows. In an actual design, please consider mounting density, the reliability of soldering, etc. and check whether performance is optimal.

unit: mm

Soldering pattern of TG5032CFN / SFN

, #3

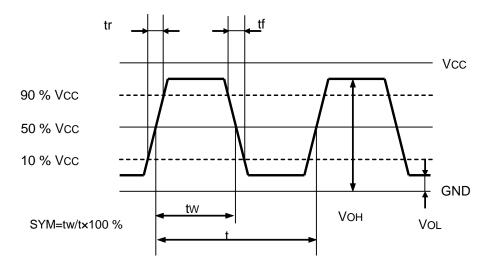


To maintain stable operation, provide a 0.1uF by-pass capacitor at a location as near as possible to the power source terminal of the crystal product (between Vcc - GND).

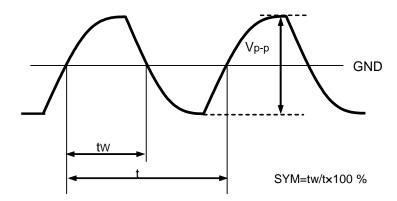


5. Timing chart

5-1) Output waveform (CMOS output)



5-2) Output waveform (Clipped sine wave output)



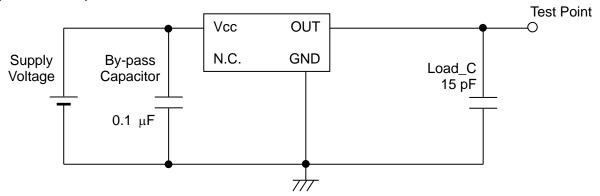
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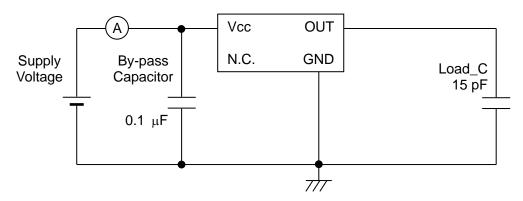
6. Test circuit

6-1) CMOS output for TCXO

1) Output Load: 15 pF



2) Current consumption



3) Conditions

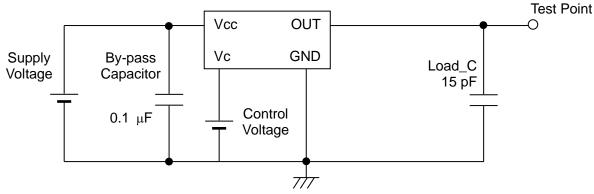
1. Oscilloscope: Impedance Min. 1 M Ω Input capacitance Max. 10 pF Band width Min. 300 MHz

- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 $\,\mu F$) is placed between V_{CC} and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- Power SupplyImpedance of power supply should be as low as possible.
- 6. GND pin should be connected to low impedance GND.

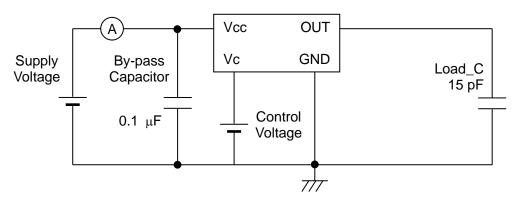


6-2) CMOS output for VC-TCXO

1) Output Load: 15 pF



2) Current consumption



3) Conditions

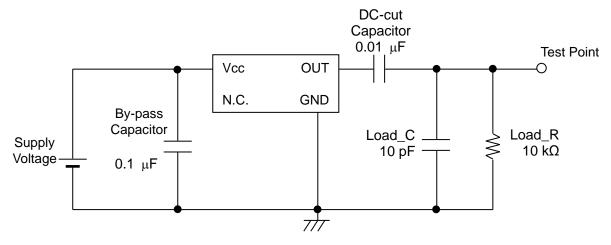
1. Oscilloscope: Impedance Min. 1 M Ω Input capacitance Max. 10 pF
Band width Min. 300 MHz

- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 $\,\mu F$) is placed between V_{CC} and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- Power Supply
 Impedance of power supply should be as low as possible.
- 6. GND pin should be connected to low impedance GND.

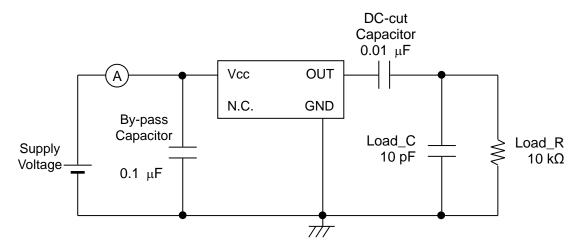


6-3) Clipped sine wave output for TCXO

1) Output Load : $10 k\Omega // 10 pF$



2) Current consumption



3) Conditions

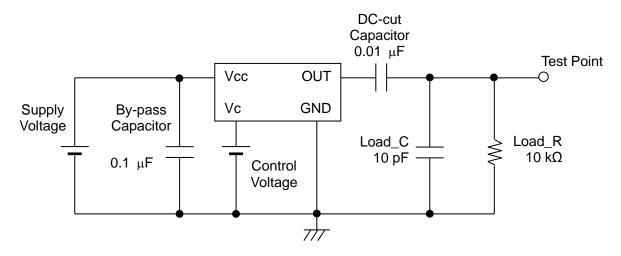
1. Oscilloscope: Impedance Min. 1 M Ω Input capacitance Max. 10 pF
Band width Min. 300 MHz

- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 $\,\mu F$) is placed between V_{CC} and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- Power SupplyImpedance of power supply should be as low as possible.
- 6. GND pin should be connected to low impedance GND.

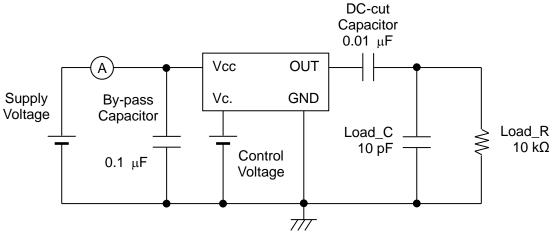


6-4) Clipped sine wave output for VC-TCXO

1) Output Load : 10 k Ω // 10 pF



2) Current consumption



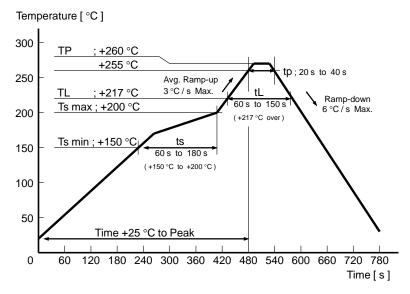
3) Conditions

1. Oscilloscope: Impedance Min. 1 M Ω Input capacitance Max. 10 pF
Band width Min. 300 MHz

- 2. Load_C includes probe capacitance.
- 3. A capacitor (By-pass: 0.1 $\,\mu F$) is placed between V_{CC} and GND, and closely to TCXO.
- 4. Use the current meter whose internal impedance value is small.
- Power Supply Impedance of power supply should be as low as possible.
- 6. GND pin should be connected to low impedance GND.



7. Reflow profile (follow to IPC / JEDEC J-STD-020D.1)



8. Packing information

(8-1) Product number last 2 digits code (00) define Quantity. 1 000 pcs/Reel.

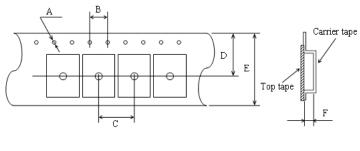
TG5032CFN: X1G005391xxxx00 (Please contact Epson for details of number xxxx)

TG5032SFN: X1G005401xxxx00

(8-2) Taping specification Subject to EIA-481 IEC-60286 JIS C0806

(1) Tape dimensions

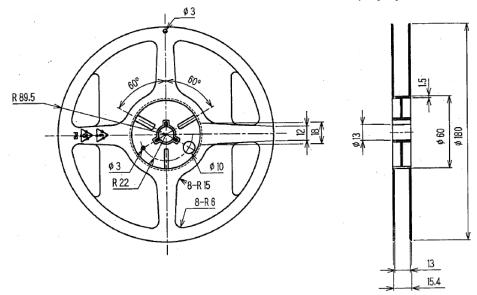
Material of the Carrier Tape: PS conduct / Material of the Top Tape: PET



Symbol	A	В	С	D	E	F		
Value	φ1.5	4.0	8.0	7.25	12.0	1.7		
					1	Unit : mm		

(2) Reel dimensions

Material of the reel: Conductive polystyrene





9. Moisture Sensitivity Level, Electro-Static Discharge

(9-1) Moisture Sensitivity Level (MSL)

Parameter	Specifications	Conditions
MSL	LEVEL1	JEDEC J-STD-020D

(9-2) Electro-Static Discharge (ESD)

Parameter	Specifications	Conditions
Human Body Model (HBM)	2 000 V Min	EIAJ ED-4701-1 C111A, 100 pF, 1.5 kΩ, 3 times
Machine Model (MM)	200 V Min	EIAJ ED-4701-1 C111, 200 pF, 0 Ω, 1 time

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10. Handling precautions

Prior to using this product, please carefully read the section entitled "Precautions" on our Web site (https://www5.epsondevice.com/en/information/#precaution) for instructions on how to handle and use the product properly to ensure optimal performance of the product in your equipment. Before using the product under any conditions other than those specified therein, please consult with us to verify and confirm that the performance of the product will not be negatively affected by use under such conditions.

In addition to the foregoing precautions, in order to avoid the deteriorating performance of the product, we strongly recommend that you DO NOT use the product under ANY of the following conditions:

- (1) Do not expose this product to excessive mechanical shock or vibration.
- (2) This product can be damaged by mechanical shock during the soldering process depending on the equipment used, process conditions, and any impact forces experienced. Always follow appropriate procedures, particularly when changing the assembly process in anyway and be sure to follow applicable process qualification standards before starting production.
- (3) These devices are sensitive to ESD, please use appropriate precautions during handling, assembly, test, shipment, and installation.
- (4) This product contains semiconductor content that should not be exposed to electromagnetic waves.
- (5) The use of ultrasonic technology for cleaning, bonding, etc. can damage the Xtal unit inside this product.

 Please carefully check for this consideration before using ultrasonic equipment for volume production with this product.
- (6) Noise and ripple on the power supply may have undesirable affects on operation and cause degradation of phase noise characteristics. Evaluate the operation of this device with appropriate power supplies carefully before use.
- (7) When applying power, ensure that the supply voltage increases monotonically for proper operation. On power down, do not reapply power until the supplies, bypass capacitors, and any bulk capacitors are completely discharged since that may cause the unit to malfunction.
- (8) Aging specifications are estimated from environmental reliability tests and expected frequency variation over time. They do not provide a guarantee of aging over the product lifecycle.
- (9) The metal cap on top of the device is directly connected to the GND terminal (pin #2). Take necessary precautions to prevent any conductor not at ground potential from contacting the cap as that could cause a short circuit to GND.
- (10)Do not route any signal lines, supply voltage lines, or GND lines underneath the area where the oscillators are mounted including any internal layers and on the opposite side of the PCB.
 To avoid any issues due to interference of other signal lines, please take care not to place signal lines
 - near the product as this may have an adverse affect on the performance of the product.
- (11)A bypass capacitor of the recommended value(s) must be connected between the Vcc and GND terminals of the product. Whenever possible, mount the capacitor(s) on the same side of the PCB and as close to the product as possible to keep the routing traces short.
- (12)Power supply connections to Vcc and GND pins should be routed as thick as possible while keeping the high frequency impedance low in order to get the best performance.
- (13) The use of a filter or similar element in series with the power supply connections to protect from electromagnetic radiation noise may increase the high frequency impedance of the power supply line and may cause the oscillator to not operate properly. Please verify the design to ensure sufficient operational margin prior to use.
- (14) Keep PCB routing from the output terminal(s) to the load as short as possible for best performance.
- (15) Do not short the output to GND as that will damage the product. Always use with an appropriate load resistor connected.
- (16) Product failures during the warranty period only apply when the product is used according to the recommended operating conditions described in the specifications. Products that have been opened for analysis or damaged will not be covered. It is recommended to store and use in normal temperature and humidity environments described in the specifications to ensure frequency accuracy and prevent moisture condensation. If the product is stored for more than one year, please confirm the pin solderability prior to use.
- (17) If the oscillation circuit is exposed to condensation, the frequency may change or oscillation may stop. Do not use in any conditions where condensation occurs.
- (18) Do not store or use the product in an environment where it can be exposed to chemical substances that are corrosive to metal or plastics such as salt water, organic solvents, chemical gasses, etc. Do not use the product when it is exposed to sunlight, dust, corrosive gasses, or other materials for long periods of time.
- (19) When using water-soluble solder flux make sure to completely remove the flux residue after soldering.

 Pay particular attention when the residues contain active halogens which will negatively affect the product and its performance.

PROMOTION OF ENVIRONMENTAL MANAGEMENT SYSTEM CONFORMING TO INTERNATIONAL STANDARDS

At Seiko Epson, all environmental initiatives operate under the Plan-Do-Check-Action (PDCA) cycle designed to achieve continuous improvements. The environmental management system (EMS) operates under the ISO 14001 environmental management standard.

All of our major manufacturing and non-manufacturing sites, in Japan and overseas, completed the acquisition of ISO 14001 certification.

ISO 14000 is an international standard for environmental management that was established by the International Standards Organization in 1996 against the background of growing concern regarding global warming, destruction of the ozone layer, and global deforestation.

WORKING FOR HIGH QUALITY

In order provide high quality and reliable products and services than meet customer needs, Seiko Epson made early efforts towards obtaining ISO9000 series certification and has acquired ISO9001 for all business establishments in Japan and abroad. We have also acquired IATF 16949 certification that is requested strongly by major automotive manufacturers as standard.

IATF 16949 is the international standard that added the sector-specific supplemental requirements for automotive industry based on ISO9001.

► Explanation of the mark that are using it for the catalog



►Pb free.



► Complies with EU RoHS directive.

*About the products without the Pb-free mark.

Contains Pb in products exempted by EU RoHS directive.

(Contains Pb in sealing glass, high melting temperature type solder or other.)



▶ Designed for automotive applications such as Car Multimedia, Body Electronics, Remote Keyless Entry etc.



▶ Designed for automotive applications related to driving safety (Engine Control Unit, Air Bag, ESC etc).

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